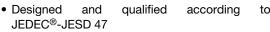


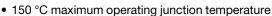
# Thyristor High Voltage, Phase Control SCR, 50 A

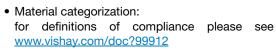


PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub>	50 A					
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V					
V <sub>TM</sub> (typ.)	1.1 V					
I <sub>GT</sub> (typ.)	40 mA					
T <sub>J</sub>	-40 °C to +150 °C					
Package	TO-247AD 3L					
Circuit configuration	Single SCR					

### **FEATURES**











ROHS COMPLIANT HALOGEN FREE

### **APPLICATIONS**

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

#### **DESCRIPTION**

The VS-50TPS12 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
V <sub>RRM</sub> /V <sub>DRM</sub>		1200	.,			
V <sub>T</sub>	50 A, T <sub>J</sub> = 125 °C	1.1	7			
I <sub>T(AV)</sub>		50				
I <sub>RMS</sub>		79	A			
I <sub>TSM</sub>		630				
dV/dt		1000	V/µs			
T <sub>.I</sub> , T <sub>Sta</sub>		-40 to +150	°C			

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA			
VS-50TPS12L-M3	1200	1300	10			



ABSOLUTE MAXIMUM RATINGS								
DADAMETED	CVMDOL	TEST CONDITIONS		VAL	UNITS			
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	DIVITS		
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 112 °C, 180° conduction half sine wa	ave	-	50			
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			-	79	А		
Peak, one-cycle non-repetitive surge current	l	10 ms sine pulse, rated V <sub>RRM</sub> applied		-	530			
reak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	Initial $T_J = T_J$	-	630			
I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	maximum	-	1405	A <sup>2</sup> s		
I-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		-	1986			
$I^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied,	T <sub>J</sub> = 125 °C	-	19 850	A <sup>2</sup> √s		
Low level value of threshold voltage	V <sub>T(TO)1</sub>			-	0.89	V		
High level value of threshold voltage	V <sub>T(TO)2</sub>	T <sub>.I</sub> = 125 °C		-	0.97	, v		
Low level value of on-state slope resistance	r <sub>t1</sub>			-	6.77	mΩ		
High level value of on-state slope resistance	r <sub>t2</sub>			-	6.32			
On atota valtaga	V	50 A, T <sub>J</sub> = 25 °C		1.2	1.32	V		
On-state voltage	V <sub>T</sub>	100 A, T <sub>J</sub> = 25 °C			1.6	V		
Rate of rise of turned-on current	dl/dt	T <sub>J</sub> = 25 °C		-	150	A/µs		
Holding current	I <sub>H</sub>	Anada ayanlır. C.V. registiye laad. T. Of		-	300			
Latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		-	350	mA		
Deverse and direct leakage current	1/1	T <sub>J</sub> = 25 °C		-	0.05	IIIA		
Reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 125 °C			10			
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , $R_g$	$g$ - $k = \infty \Omega$	-	1000	V/µs		

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Peak gate power	P <sub>GM</sub>	10 ma aina nula	e, no voltage reapplied	-	10	W
Average gate power	P <sub>G(AV)</sub>	TO THIS SITTLE PURS	e, no voltage reapplied	-	2.5	l vv
Peak gate current	I <sub>GM</sub>					
Peak negative gate voltage	-V <sub>GM</sub>			-	10	
		T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load	-	1.6	V
Required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C		-	1.5	V
		T <sub>J</sub> = 150 °C		-	1	
		T <sub>J</sub> = -40 °C		-	160	
Required DC gate to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	45	100	mA
		T <sub>J</sub> = 150 °C		-	60	
DC gate voltage not to trigger	$V_{GD}$	T 450 00 W		-	0.2	V
DC gate current not to trigger	$I_{GD}$	$I_{\rm J} = 150^{\circ} \rm C, V_{\rm D}$	T <sub>J</sub> = 150 °C, V <sub>DRM</sub> = rated value		3	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Turn-on time	t <sub>gt</sub>	$I_T = 50 \text{ A}, V_D = 50 \% V_{DRM}, I_{gt} = 300 \text{ mA}, T_J = 25 °C$	1.5	
Turn-off time	t <sub>q</sub>	$\begin{array}{l} I_T = 50 \text{ A, V}_D = 80 \text{ \% V}_{DRM}, \text{dV/dt} = 20 \text{ V/µs, t}_p = 200 \text{ µs} \\ I_{gt} = 100 \text{ mA, dI/dt} = 10 \text{ A/µs, V}_R = 100 \text{ V, T}_J = 150 \text{ °C} \\ \end{array}$	92	μs



THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS		
Maximum junction and storag	e temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40	150	°C		
Maximum thermal resistance,	aximum thermal resistance, junction to case			-	0.35			
Maximum thermal resistance,	Maximum thermal resistance, junction to ambient			-	40	°C/W		
Typical thermal resistance, ca	Typical thermal resistance, case to heatsink		Mounting surface, smooth, and greased	0.2	-			
Mounting torque	minimum			6	(5)	kgf · cm		
woulding torque	maximum			12	(10)	(lbf · in)		
Marking device			Case style Super TO-247AD 3L	50TPS12L		L		

△R <sub>thJ-HS</sub> CONDUCTION PER JUNCTION											
DEVICE	SINE HALF-WAVE CONDUCTION RECTANGULAR WAVE CONDUCTION					SINE HALF-WAVE CONDUCTION RECTANGULAR WAVE CONDUCTION			UNITS		
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-50TPS12L-M3	0.143	0.166	0.208	0.299	0.490	0.099	0.168	0.223	0.311	0.494	°C/W

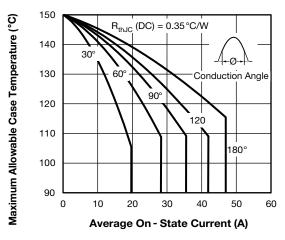


Fig. 1 - Current Rating Characteristics

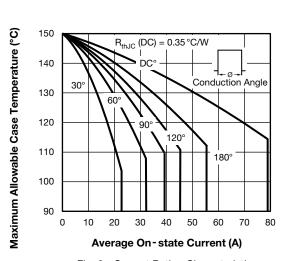


Fig. 2 - Current Rating Characteristics

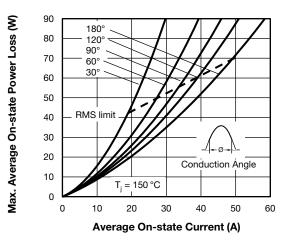


Fig. 3 - On-State Power Loss Characteristics

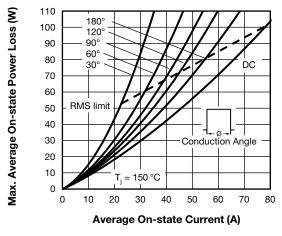


Fig. 4 - On-State Power Loss Characteristics



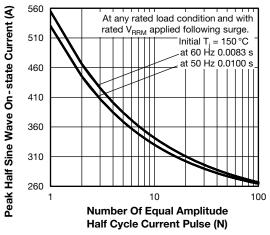


Fig. 5 - Maximum Non-Repetitive Surge Current

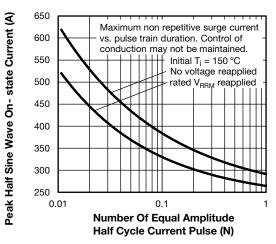


Fig. 6 - Maximum Non-Repetitive Surge Current

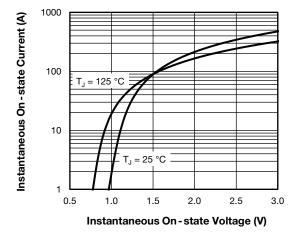


Fig. 7 - On-State Voltage Drop Characteristics

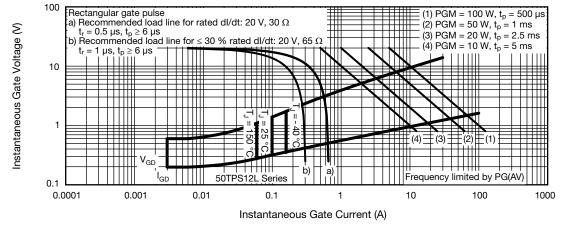


Fig. 8 - Gate Characteristics

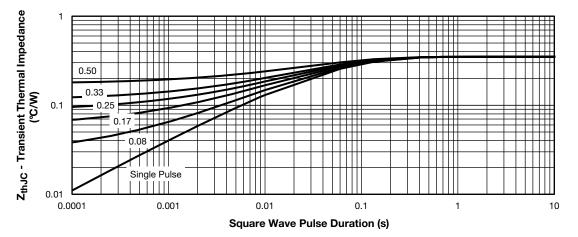


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

### **ORDERING INFORMATION TABLE**

Device code	VS-	50	Т	Р	S	12	L	-M3
	1)	2	3	4	5	6	7	8

- 1 Vishay Semiconductors product
- 2 Current code (50 = 50 A)
- **3** Circuit configuration:

T = thyristor

- 4 P = TO-247AD 3L package
- 5 Type of silicon:

S = standard recovery rectifier

- 6 Voltage code (12 = 1200 V)
- 7 Package L = long lead
- 8 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

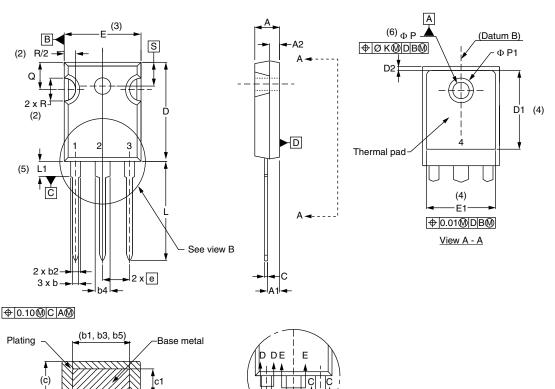
ORDERING INFORMATION (example)						
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-50TPS12L-M3	25	contact factory	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95626				
Part marking information	www.vishay.com/doc?95007				



## **TO-247AD 3L**

### **DIMENSIONS** in millimeters and inches



Section C - C, D - D, E - E								
SYMBOL	MILLIN	IETERS	INC	HES	NOTES			
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES			
Α	4.65	5.31	0.183	0.209				
A1	2.21	2.59	0.087	0.102				
A2	1.50	2.49	0.059	0.098				
b	0.99	1.40	0.039	0.055				

0.039

0.065

0.065

0.102

0.102

0.015

0.015

0.776

0.515

0.053

0.094

0.092

0.135

0.133

0.035

0.033

0.815

(h h2 h4)

:5	

View B

SYMBOL	MILLIMILILIA		INCLIES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØΚ	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		
•	•		•		•

INCHES

MILLIMETERS

### Notes

b1

b2

b3

b4

b5

С

с1

D

D1

(1) Dimensioning and tolerancing per ASME Y14.5M-1994

1.35

2.39

2.34

3.43

3.38

0.89

0.84

20.70

- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

3

- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1

0.99

1.65

1.65

2.59

2.59

0.38

0.38

19.71

13.08

- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4



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Vishay

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